

Low voltage high performance NPN power transistor

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed

Applications

- Emergency lighting
- LED drive
- Motherboard and hard disk drive
- Mobile equipment
- DC-DC converter, voltage regulation

Description

The device is a NPN transistor manufactured using new "PB-HCD" (power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

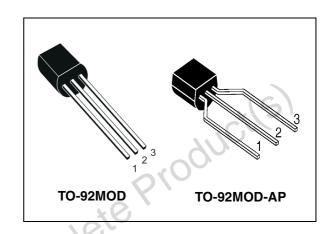


Figure 1. Internal schematic diagram

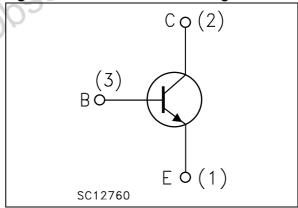


Table 1. Device summary

Order codes	Marking	Package	Packaging
2STL1525	2STL1525	TO-92MOD	Bag
2STL1525-AP	2STL1525	TO-92MOD-AP	Ammopack

December 2010 Doc ID 16054 Rev 2 1/8

Electrical ratings 2STL1525

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CEX}	Collector-emitter voltage (V _{BE} = -1.5 V)	95	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	25	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	5	٧
I _C	Collector current	5	Α
I _{CM}	Collector peak current (t _P < 5 ms)	10	Α
I _B	Base current	1 . (9	A
P _{TOT}	Total dissipation at T _{amb} = 25 °C	1.5	W
T _{STG}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

S	ymbol	Parameter	Value	Unit
	R_{thJA}	Thermal resistance junction-ambient max	83	°C/W
		oduci(S)		
	01	OQIC		
100	3			
Obsolete				

2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 50 V			0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 4 V			0.1	μА
V _{(BR)CEX}	Collector-emitter breakdown voltage (V _{BE} = -1.5 V)	I _C = 1 mA	95	401		V
V _{(BR)CEO} (1)	Collector-emitter breakdown voltage (I _B = 0)	I _C = 10 mA	25	O.		V
V _{(BR)EBO}	Emitter-base breakdown voltage $(I_C = 0)$	Ι _Ε = 100 μΑ	5			V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} I_{C} &= 0.5 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 3 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 5 \text{ A} & V_{CE} = 5 \text{ V} \end{split}$	150 100	150	500	
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 3 \text{ A}$ $I_B = 300 \text{ mA}$ $I_C = 3.5 \text{ A}$ $I_B = 40 \text{ mA}$		220	500	mV mV
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 3 A I _B = 300 mA			1.2	V
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V, f = 1 MHz		20		pF
fτ	Transition frequency	V _{CE} = 10 V I _C = 50 mA		120		MHz
t _{on} t _{off}	Resistive load Turn-on time Turn-off time	$I_C = 1.5 \text{ A}$ $V_{CC} = 10 \text{ V}$ $I_{B1} = -I_{B2} = 150 \text{ mA}$		60 450		ns ns

^{1.} Pulse test: pulse duration \leq 300 μ s, duty cycle \leq 2%

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Package mechanical data 3

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 5. TO-92MOD mechanical data

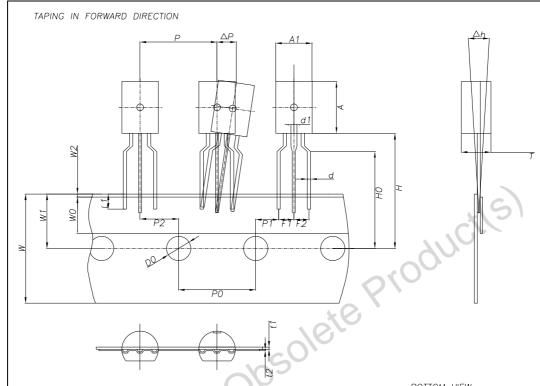
Table 5. TO-92N	MOD mechanical data		AUCL		
Dim.		mm.			
	Min.	Тур.	Max.		
A	4.7	1010	5.1		
A1	1.730	-0/	2.030		
b	0.4	0	0.6		
b1	0.9		1.1		
С	0.4		0.5		
D	5.8		6.2		
D1	4.0				
E	8.4		8.8		
e		1.5			
e1	2.9		3.1		
L	13.8		14.2		
К			1.6		
h	0.0		0.380		

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Figure 2. TO-92MOD drawing mechanical data

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TO-92MOD-AP ammopack dimension



Tanina	in	Forward	Direction

BOTTOM VIEW

		ITEM	SYMBOL	VALUE & TOLERANCE
		Body Width	A1	6.0 ± 0.2
		Body Eigth	Α	8.6 ± 0.2
		Body Thickness	T	4.9 ± 0.2
		Lead Wire Diameter	d	0.5 ± 0.05
		Lead Wire Diameter 1	d1	1.0 ± 0.05
	- 4	Pitch of component	P	12.7 ± 0.3
		Feed Hole Pitch	P0	12.7 ± 0.2
		Hole center to component center	P2	6.35 ± 0.3
	, e	Lead to lead distance	F1, F2	2.5 ± 0.3
		Component alignment F-R		0 ± 1.0
10		Type width	W	18.0 +1.0, -0.5
Obsole		Hole down tape width	WO	6.0 ± 0.5
		Hole position	W1	9.0 ± 0.5
		Hole down tape position	W2	1.0 MAX
		Height of component from tape center	Н	19.0 ± 1.0
		Lead wire clinch height	HO	16.0 ± 0.5
		Lead wire (tape portion)	L1	2.5 MIN
		Feed hole diameter	DO DO	4.0 ± 0.2
		Taped Lead Thickness	t 1	0.4 ± 0.05
		Carrier tape Thickness	t2	0.2 ± 0.05
		Position of Hole	P1	3.85 ± 0.03
		Component alignment	ΔP	0 ± 1.0
				Unit: mm

^{*}Dimensions in mm

8231868_B

^{*}Cumulative pitch error: 1.0mm/20 pitches

^{*}Groung paper tape: 0.5mm+/-0.1

2STL1525 Revision history

4 Revision history

Table 6. Document revision history

	Date	Revision	Changes
	31-Jul-2009	1	Initial release.
	01-Dec-2010	2	Document status promoted from preliminary data to datasheet. Updated package mechanical data <i>Table 5 on page 4</i> and <i>Figure 2 on page 5</i> .
Obsole	ie Pro	ducti	obsolete Product(s)

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